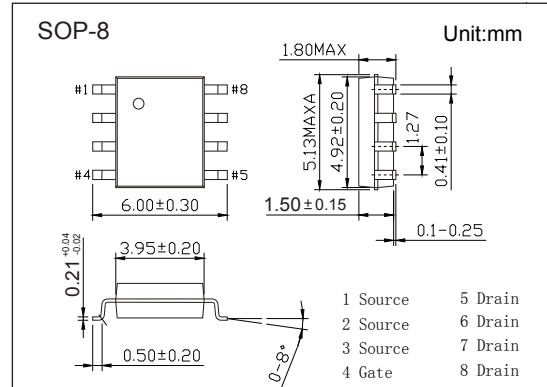
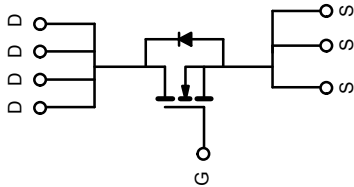


N-Channel MOSFET

AO4880

■ Features

- $V_{DS} = 40V$
- $I_D = 20A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 17m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 22m\Omega$ ($V_{GS} = 4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	20	A
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = 250\mu A, V_{GS} = 0V$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1		2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$			17	$m\Omega$
		$V_{GS} = 4.5V, I_D = 20A$			22	

■ Marking

Marking	4880 KC****
---------	----------------